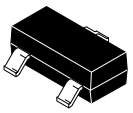
MMBT2369LT1G, SMMBT2369LT1G, MMBT2369ALT1G, SMMBT2369ALT1G

Switching Transistors

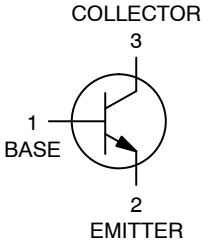
NPN Silicon

ON Semiconductor®

http://onsemi.com



SOT−23
CASE 318
STYLE 6



Features

- AEC−Q101 Qualified and PPAP Capable
- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements
- These Devices are Pb−Free, Halogen Free/BFR Free and are RoHS Compliant*

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector − Emitter Voltage	V_{CEO}	15	Vdc
Collector − Emitter Voltage	V_{CES}	40	Vdc
Collector − Base Voltage	V_{CBO}	40	Vdc
Emitter − Base Voltage	V_{EBO}	4.5	Vdc
Collector Current − Continuous	I_C	200	mAdc

THERMAL CHARACTERISTICS

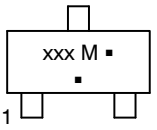
Characteristic	Symbol	Max	Unit
Total Device Dissipation FR−5 Board (Note 1) T_A = 25°C Derate above 25°C	P_D	225 1.8	mW mW/°C
Thermal Resistance, Junction−to−Ambient	$R_{\theta JA}$	556	°C/W
Total Device Dissipation Alumina Substrate, (Note 2) T_A = 25°C Derate above 25°C	P_D	300 2.4	mW mW/°C
Thermal Resistance, Junction−to−Ambient	$R_{\theta JA}$	417	°C/W
Junction and Storage Temperature	T_J, T_{stg}	−55 to +150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. FR−5 = 1.0 × 0.75 × 0.062 in.
2. Alumina = 0.4 × 0.3 × 0.024 in. 99.5% alumina.

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

MARKING DIAGRAM



xxx = M1J or 1JA
M = Date Code*
▪ = Pb−Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping†
MMBT2369LT1G	SOT−23 (Pb−Free)	3,000 / Tape & Reel
SMMBT2369LT1G	SOT−23 (Pb−Free)	3,000 / Tape & Reel
MMBT2369ALT1G	SOT−23 (Pb−Free)	3,000 / Tape & Reel
SMMBT2369ALT1G	SOT−23 (Pb−Free)	3,000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector – Emitter Breakdown Voltage (Note 3) (I_C = 10 mAdc, I_B = 0)	$V_{(BR)CEO}$	15	–	–	Vdc
Collector – Emitter Breakdown Voltage (I_C = 10 μAdc, V_{BE} = 0)	$V_{(BR)CES}$	40	–	–	Vdc
Collector – Base Breakdown Voltage (I_C = 10 μAdc, I_E = 0)	$V_{(BR)CBO}$	40	–	–	Vdc
Emitter – Base Breakdown Voltage (I_E = 10 μAdc, I_C = 0)	$V_{(BR)EBO}$	4.5	–	–	Vdc
Collector Cutoff Current (V_{CB} = 20 Vdc, I_E = 0) (V_{CB} = 20 Vdc, I_E = 0, T_A = 150°C)	I_{CBO}	– –	– –	0.4 30	μAdc
Collector Cutoff Current MMBT2369A (V_{CE} = 20 Vdc, V_{BE} = 0)	I_{CES}	–	–	0.4	μAdc
ON CHARACTERISTICS					
DC Current Gain (Note 3) MMBT2369, SMMBT2369 (I_C = 10 mAdc, V_{CE} = 1.0 Vdc) MMBT2369A, SMMBT2369A (I_C = 10 mAdc, V_{CE} = 1.0 Vdc) MMBT2369A, SMMBT2369A (I_C = 10 mAdc, V_{CE} = 0.35 Vdc) MMBT2369A, SMMBT2369A (I_C = 10 mAdc, V_{CE} = 0.35 Vdc, T_A = −55°C) MMBT2369A, SMMBT2369A (I_C = 30 mAdc, V_{CE} = 0.4 Vdc) MMBT2369, SMMBT2369 (I_C = 100 mAdc, V_{CE} = 2.0 Vdc) MMBT2369A, SMMBT2369A (I_C = 100 mAdc, V_{CE} = 1.0 Vdc)	h_{FE}	40 – 40 20 30 20 20	– – – – – – –	120 120 – – – – –	–
Collector – Emitter Saturation Voltage (Note 3) MMBT2369, SMMBT2369 (I_C = 10 mAdc, I_B = 1.0 mAdc) MMBT2369A, SMMBT2369A (I_C = 10 mAdc, I_B = 1.0 mAdc) MMBT2369A, SMMBT2369A (I_C = 10 mAdc, I_B = 1.0 mAdc, T_A = +125°C) MMBT2369A, SMMBT2369A (I_C = 30 mAdc, I_B = 3.0 mAdc) MMBT2369A, SMMBT2369A (I_C = 100 mAdc, I_B = 10 mAdc)	$V_{CE(sat)}$	– – – – –	– – – – –	0.25 0.20 0.30 0.25 0.50	Vdc
Base – Emitter Saturation Voltage (Note 3) MMBT2369/A, SMMBT2369/A (I_C = 10 mAdc, I_B = 1.0 mAdc) MMBT2369A, SMMBT2369A (I_C = 10 mAdc, I_B = 1.0 mAdc, T_A = −55°C) MMBT2369A, SMMBT2369A (I_C = 30 mAdc, I_B = 3.0 mAdc) MMBT2369A, SMMBT2369A (I_C = 100 mAdc, I_B = 10 mAdc)	$V_{BE(sat)}$	0.7 – – –	– – – –	0.85 1.02 1.15 1.60	Vdc
SMALL−SIGNAL CHARACTERISTICS					
Output Capacitance (V_{CB} = 5.0 Vdc, I_E = 0, f = 1.0 MHz)	C_{obo}	–	–	4.0	pF
Small Signal Current Gain (I_C = 10 mAdc, V_{CE} = 10 Vdc, f = 100 MHz)	h_{fe}	5.0	–	–	–
SWITCHING CHARACTERISTICS					
Storage Time (I_{B1} = I_{B2} = I_C = 10 mAdc)	t_s	–	5.0	13	ns
Turn−On Time (V_{CC} = 3.0 Vdc, I_C = 10 mAdc, I_{B1} = 3.0 mAdc)	t_{on}	–	8.0	12	ns
Turn−Off Time (V_{CC} = 3.0 Vdc, I_C = 10 mAdc, I_{B1} = 3.0 mAdc, I_{B2} = 1.5 mAdc)	t_{off}	–	10	18	ns

3. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

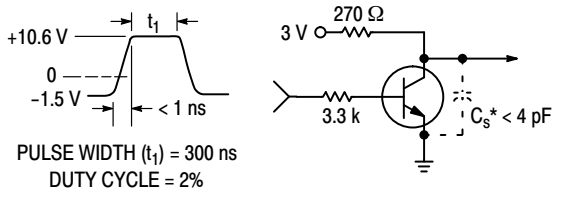


Figure 1. t_{on} Circuit – 10 mA

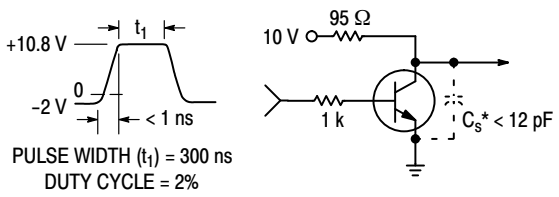


Figure 2. t_{on} Circuit – 100 mA

*Total shunt capacitance of test jig and connectors.

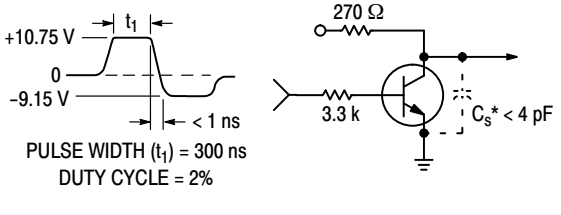


Figure 3. t_{off} Circuit – 10 mA

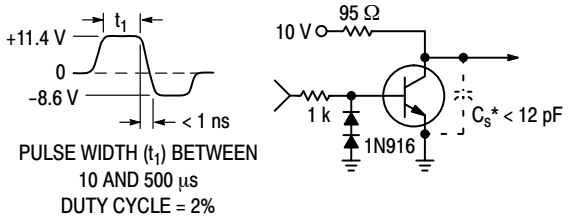


Figure 4. t_{off} Circuit – 100 mA

*Total shunt capacitance of test jig and connectors.

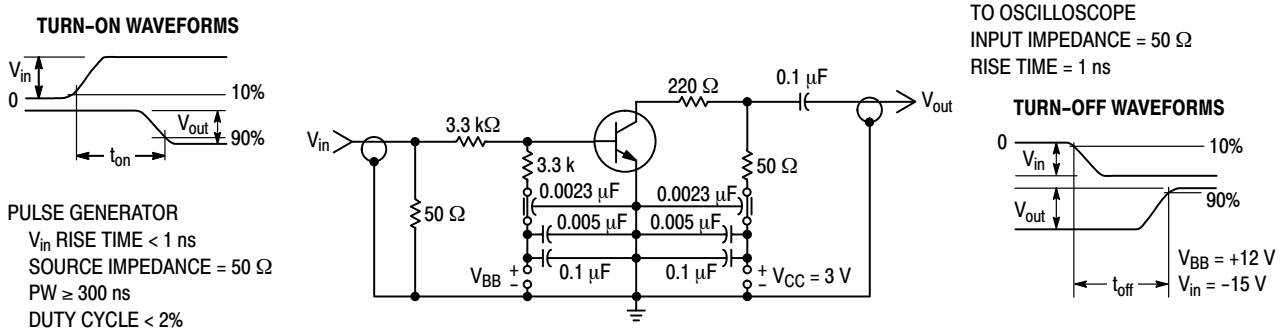


Figure 5. Turn−On and Turn−Off Time Test Circuit

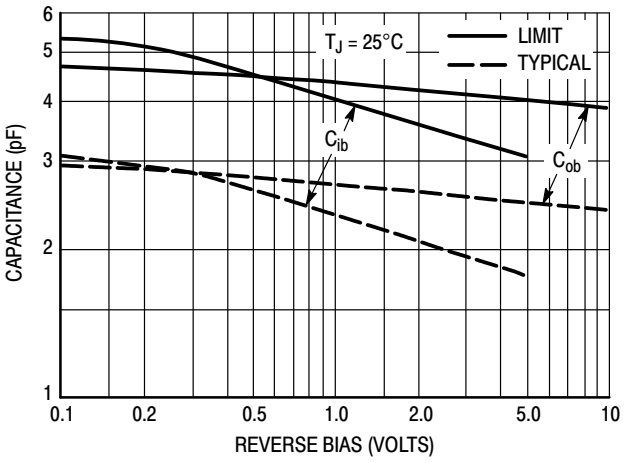


Figure 6. Junction Capacitance Variations

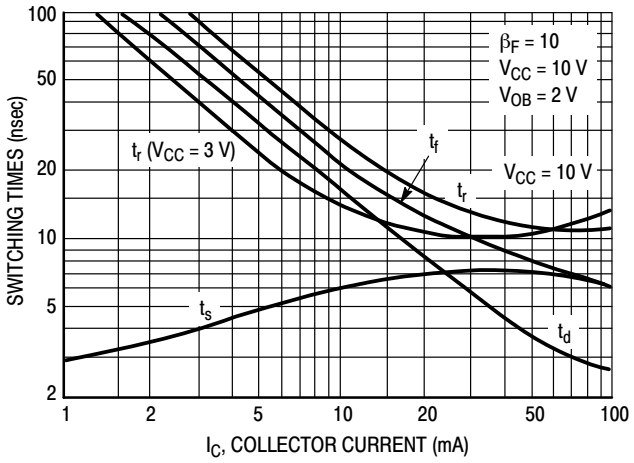


Figure 7. Typical Switching Times

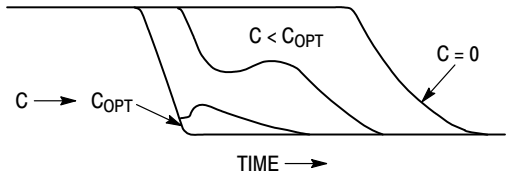


Figure 8. Turn−Off Waveform

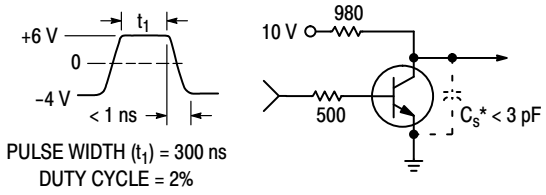


Figure 9. Storage Time Equivalent Test Circuit

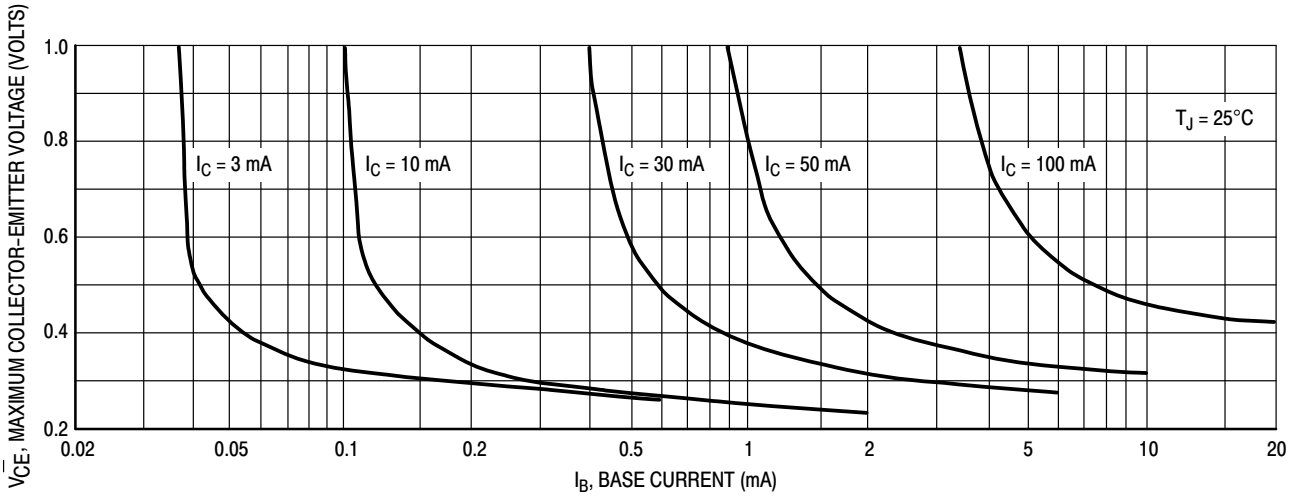


Figure 10. Maximum Collector Saturation Voltage Characteristics

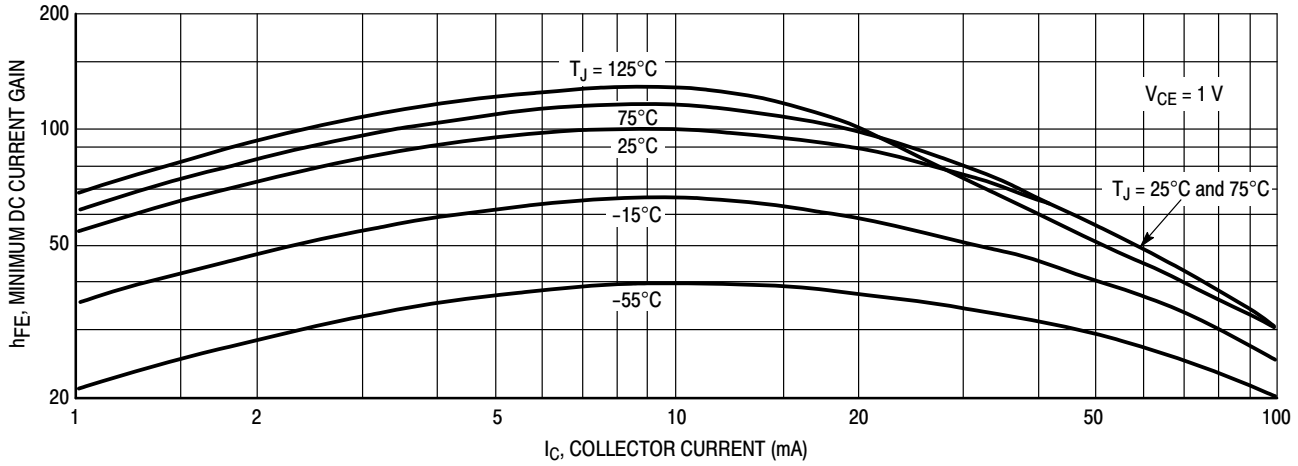


Figure 11. Minimum Current Gain Characteristics

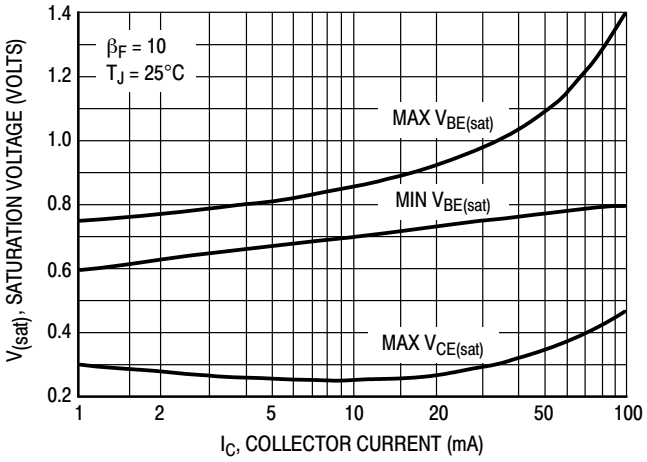
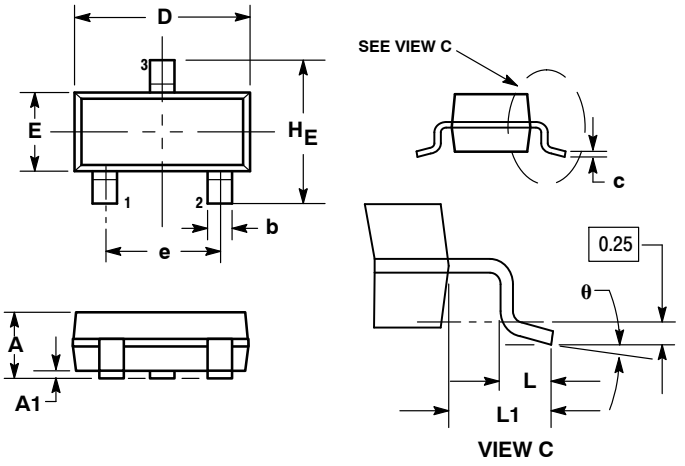


Figure 12. Saturation Voltage Limits

PACKAGE DIMENSIONS

SOT−23 (TO−236)
CASE 318−08
ISSUE AP

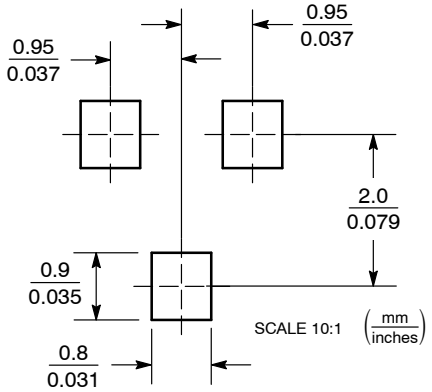


NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
A	0.89	1.00	1.11	0.035	0.040	0.044
A1	0.01	0.06	0.10	0.001	0.002	0.004
b	0.37	0.44	0.50	0.015	0.018	0.020
c	0.09	0.13	0.18	0.003	0.005	0.007
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.081
L	0.10	0.20	0.30	0.004	0.008	0.012
L1	0.35	0.54	0.69	0.014	0.021	0.029
H_E	2.10	2.40	2.64	0.083	0.094	0.104
θ	0°	−−−	10°	0°	−−−	10°

STYLE 6:
PIN 1. BASE
2. EMITTER
3. COLLECTOR

SOLDERING FOOTPRINT



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MMBT2369LT1/D

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